

Substitute for form 1449A/PTO
**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
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PTO
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TRADEMARK OFFICE

Sheet 1 of 3

Complete If Known	
Application Number	10/075484
Filing Date	February 12, 2002
First Named Inventor	Bhattacharyya, Arup
Group Art Unit	2818
Examiner Name	Phan, Trong

Attorney Docket No: 1303.043US1

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DATE CONSIDERED *3/30/04*

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 PATENT & TRADEMARK OFFICE 809
 Sheet 1 of 1

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